

**DESCRIPTION:**

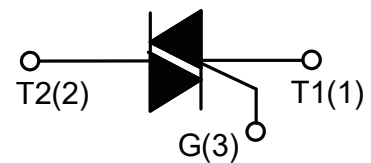
With high ability to withstand the shock loading of large current, T410-600B series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.



TO-252

**MAIN FEATURES**

Symbol	Value	Unit
$V_{DRM}/V_{RRM}$	600/800	V
$I_{T(RMS)}$	4	A


**ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40 - 150	°C
Operating junction temperature range		$T_j$	-40 - 125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )		$V_{DRM}$	600/800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )		$V_{RRM}$	600/800	V
RMS on-state current	TO-252 ( $T_C=100^\circ\text{C}$ )	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		$I_{TSM}$	40	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )		$I^2t$	8	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2\times I_{GT}$ )		$di/dt$	50	$\text{A}/\mu\text{s}$
Peak gate current		$I_{GM}$	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		$P_{GM}$	5	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
$I_{GT}$	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	5	10	35	50	mA
$V_{GT}$		I - II -III	MAX	1.5				V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2				V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX	10	20	50	70	mA
		II		15	35	60	80	
$I_H$	$I_T=100\text{mA}$		MAX	10	15	35	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	50	100	400	1000	V/ $\mu\text{s}$

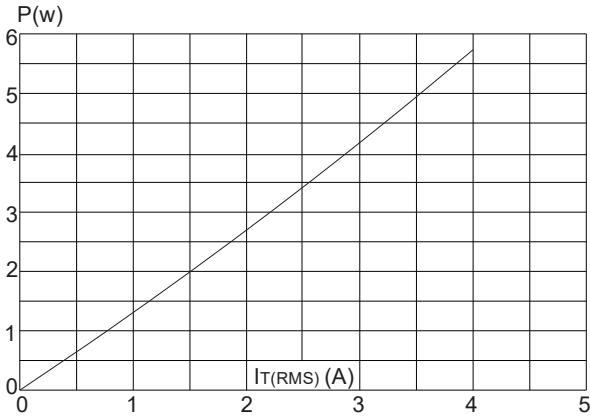
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=5.5\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	0.75	mA

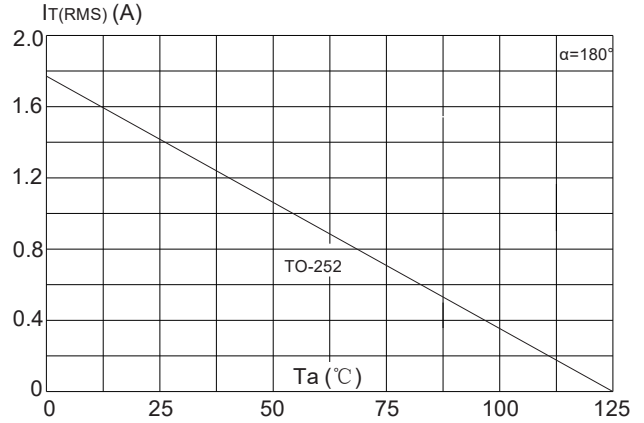
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252	2.8	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient		70	

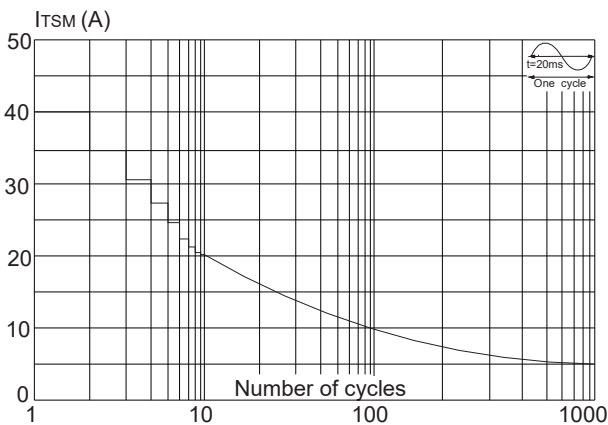
**FIG.1:** Maximum power dissipation versus RMS on-state current



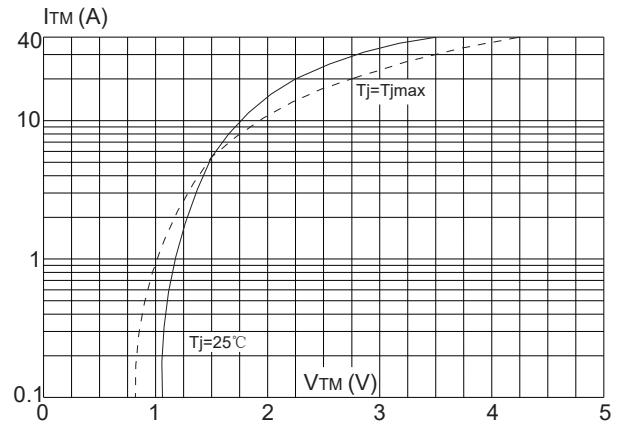
**FIG.2:** RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35 $\mu$ m)(full cycle)

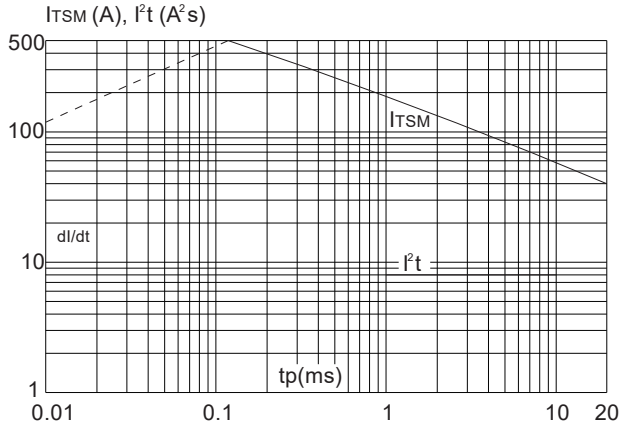
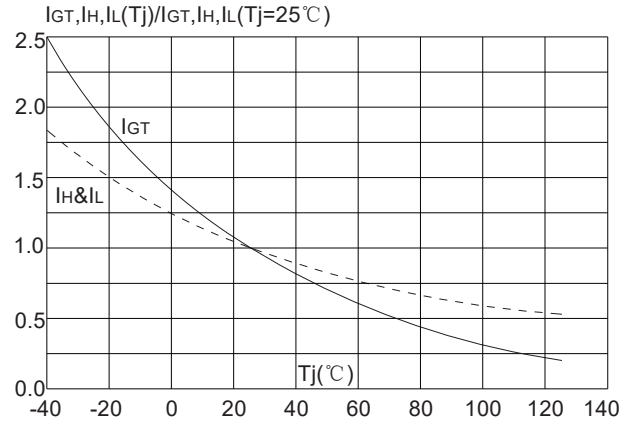


**FIG.3:** Surge peak on-state current versus number of cycles



**FIG.4:** On-state characteristics (maximum values)



**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$  and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )

**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature


## SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ( $T_{s(\text{min})}$ )	+150°C
	-Temperature Max ( $T_{s(\text{max})}$ )	+200°C
	-Time (Min to Max) ( $t_s$ )	60-180 secs.
Average ramp up rate (Liquidus Temp ( $T_L$ ) to peak)		3°C/sec. Max
$T_{s(\text{max})}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature( $T_L$ ) (Liquidus)	+217°C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_p$ )		+260(+0/-5)°C
Time within 5°C of actual Peak Temp ( $t_p$ )		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp ( $T_p$ )		8 min. Max
Do not exceed		+260°C

